

# SG01XXL-8ISO90

Broadband SiC based UV photodiode  $A = 36 \text{ mm}^2$ 

# GENERAL FEATURES

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### Properties of the SGo1XXL-8ISO90 UV photodiode

- Broadband UVA+UVB+UVC, PTB reported high chip stability
- Active Area A = 36 mm<sup>2</sup>
- TO8 hermetically sealed metal housing, two isolated pins in a circle
- 10µW/cm² peak radiation results a current of approx. 468 nA

### About the material Silicon Carbide (SiC)

SiC provides the unique property of extreme radiation hardness, near-perfect visible blindness, low dark current, high speed and low noise. These features make SiC the best available material for visible blind semiconductor UV detectors. The SiC detectors can be permanently operated at up to 170°C (338°F). The temperature coefficient of signal (responsivity) is also low, < 0,1%/K. Because of the low noise (dark current in the fA range), very low UV radiation intensities can be measured reliably. Please note that this device needs an appropriate amplifier (see typical circuit on page 3).

#### **Options**

SiC photodiodes are available with five different active chip areas from 0,06 mm<sup>2</sup> up to 4,00 mm<sup>2</sup>. Standard version is broadband UVA-UVB-UVC. Four filtered versions lead to a tighter sensitivity range. All photodiodes have a hermetically sealed metal housing (TO type), either a 5,5 mm diameter TO18 housing or a 9,2 mm TO5 housing. Further option is either a 2 pin header (1 isolated, 1 grounded) or a 3 pin header (2 isolated, 1 grounded).

### NOMENCLATURE

| SG01                              |   |   |  |  |
|-----------------------------------|---|---|--|--|
| S, M, D, L, XL                    | nothing, A, B, C or E   | 18, 18ISO90, 18S, 5, 5ISO90   | nothing, Lens,<br>MEGA, GIGA                     |  |
| Chip area                         | Spectral response   | Housing   | Special  |  |
| <b>S</b> 0,06 mm <sup>2</sup>     | nothing = broadband<br>$\lambda_{\text{max}} = 280 \text{ nm}$ $\lambda_{\text{S10\%}} = 221 \text{ nm} \dots 358 \text{ nm}$ | <b>18</b> 2-pin TO18 housing, h = 5,2 mm, 1 pin isolated, 1 pin grounded                  | Lens with concentrating                          |  |
| <b>M</b><br>0,20 mm <sup>2</sup>  | <b>A = UVA</b> $\lambda_{max} = 331 \text{ nm}  \lambda_{S10\%} = 309 \text{ nm} \dots 367 \text{ nm}$                        | <b>18ISO90</b> 3-pin TO18 housing, h = 5,2 mm, 2 pins isolated, 1 pin grounded            | lens, TO5 only                                   |  |
| <b>D</b> 0,50 mm <sup>2</sup>     | <b>B = UVB</b> $\lambda_{\text{max}} = 280 \text{ nm}  \lambda_{\text{S10\%}} = 231 \text{ nm } 309 \text{ nm}$               | <b>185</b> 2-pin TO18 housing, h = 3,7 mm, 1 pin isolated, 1 pin grounded                 | MEGA with attenuator up to 0,5 W/cm <sup>2</sup> |  |
| L<br>1,00 mm²                     | $C = UVC$ $\lambda_{max} = 275 \text{ nm}$ $\lambda_{S10\%} = 225 \text{ nm } 287 \text{ nm}$                                 | 5 2-pin TO5 housing, h = 4,3 mm for broadband; h = 6,7 mm for filtered UVA, UVB, UVC, UVI | GIGA   |  |
| <b>XL</b><br>4,00 mm <sup>2</sup> | E = UV-Index spectral response according to CIEo87  | <b>5ISO90</b> 3-pin TO5 housing, h = 4,2 mm, 2 pins isolated, 1 pin grounded              | with attenuator<br>up to 7 W/cm <sup>2</sup>     |  |

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Add: 16/F, Bldg. #3, Zhongke Mansion, No.1 Hi-Tech S. Rd, Hi-Tech Park South, Shenzhen, Guangdong, 518067 P.R.China

Tel: + 86-755-83289036

Fax: +86-755-83289052

E-mail: sales@isweek.com



# SG01XXL-8ISO90

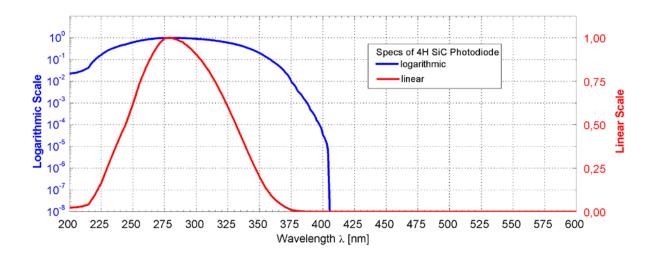
Broadband SiC based UV photodiode A = 36 mm<sup>2</sup>

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# **SPECIFICATIONS**

| Parameter                                | Symbol                 | Value              | Unit             |
|--|------------------------|--------------------|------------------|
| Spectral Characteristics                 |                        |                    |                  |
| Typical Responsivity at Peak Wavelength  | $S_{max}$              | 0,130              | AW <sup>-1</sup> |
| Wavelength of max. Spectral Responsivity | $\lambda_{\text{max}}$ | 280                | nm               |
| Responsivity Range ( $S=0,1*S_{max}$ )   | _                      | 221 358            | nm               |
| Visible Blindness $(S_{max}/S_{>405nm})$ | VB                     | > 10 <sup>10</sup> | -                |
| General Characteristics (T=25°C)         |                        |                    |                  |
| Active Area                              | Α                      | 36                 | mm²              |
| Dark Current (1V reverse bias)           | $I_d$                  | 120                | fA               |
| Capacitance                              | С                      | 9000               | pF               |
| Short Circuit (10µW/cm² at peak)         | lo                     | 468                | nA               |
| Temperature Coefficient                  | $T_c$                  | < 0,1              | %/K              |
| Maximum Ratings                          |                        |                    |                  |
| Operating Temperature                    | $T_{opt}$              | −55 <b></b> +170   | °C               |
| Storage Temperature                      | $T_{stor}$             | −55 <b></b> +170   | °C               |
| Soldering Temperature (3s)               | $T_{sold}$             | 260                | °C               |
| Reverse Voltage                          | $V_{Rmax}$             | 20                 | V                |

## NORMALIZED SPECTRAL RESPONSIVITY



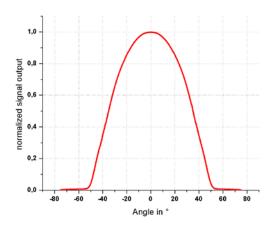


# SG01XXL-8ISO90

Broadband SiC based UV photodiode A = 36 mm<sup>2</sup>

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# FIELD OF VIEW

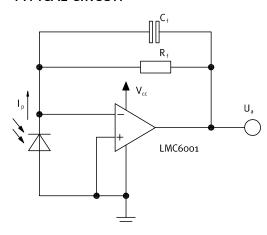


#### Measurement Setup:

lamp aperture diameter: 10 mm distance lamp aperture to second aperture: 17 mm second aperture diameter: 10 mm distance second aperture to detector: 93 mm

pivot level = top surface of the photodiode window

# TYPICAL CIRCUIT



#### Calculations and Limits:

$$U_a = \ I_p x \ R_f = \ o \ ... \ \sim \ V_{cc}$$

 $U_{a,max}$  depends on load and amplifier type

$$R_f = 10k\Omega$$
 ...  $\sim 10G\Omega$ ,  $C_f \ge 3pF$   
Recommendation:  $R_f \times C_f \ge 10^{-3}s$   
 $I_{p,max} = U_{a,max} \div R_f$ 

Bandwidth = DC ... 
$$\frac{1}{2\pi \times R_f \times C_f}$$

#### Example

 $I_p = 20$ nA,  $R_f = 100$ M $\Omega$ ,  $C_f = 100$  pF  $U_a = 20$  x  $10^9$ A x 100 x  $10^6$  $\Omega = 2$ V